

Plastic-Encapsulate Diodes

Schottky barrier Diode

FEATURES

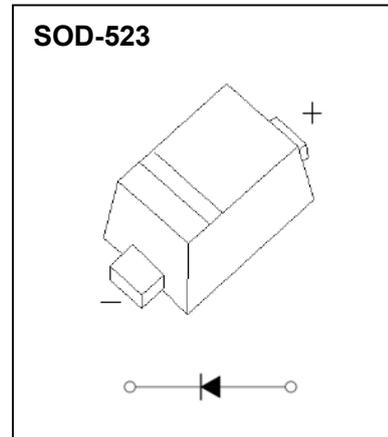
- Small surface mounting type
- Low I_R
- High reliability

MARKING: B



B=Device code

The marking bar indicates the cathode



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	200	mA
Non-repetitive Peak Forward Surge Current@t=8.3ms	I_{FSM}	1	A
Power dissipation	P_D	150	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	667	°C/W
Operating Junction Temperature Range	T_j	-40 ~ +125	°C
Storage Temperature Range	T_{stg}	-55 ~ +150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_F			0.6	V	$I_F=200mA$
Reverse current	I_R			1	μA	$V_R=10V$

Typical Characteristics
